

**In the Claims**

This listing of claims will replace all prior versions, and listings, of claims in the specification:

**Listing of Claims**

1-8. (Cancelled)

9. (Currently Amended) A thin film transistor (TFT) structure, comprising:

a plurality of stacked structures on a substrate, said plurality of stacked structures including a first conducting layer, an insulation layer, an amorphous silicon layer and an ohmic contact layer;

a photo-imagable layer between said plurality of stacked structures so as to be contact with the first conducting layer, the insulation layer, the amorphous silicon layer and the ohmic contact layer;

a source electrode and a drain electrode on said photo-imagable layer, wherein said source electrode is connected to a portion of said amorphous silicon layer and said drain electrode is connected to another portion of said amorphous silicon layer;

a passivation layer on said amorphous silicon layer, said source electrode and said drain electrode; and

a transparent electrode on said passivation layer and electrically connected to one of said source electrode and said drain electrode.

10. (Cancelled)

11. (Original) The TFT structure according to claim 9, wherein said first conducting layer is a gate electrode.

12. (Cancelled)

13. (Currently Amended) A thin film transistor (TFT) structure, comprising:  
a plurality of first stacked structures and a plurality of second stacked structures on a substrate, wherein each first stacked structure includes a first conducting layer, an insulation layer, an amorphous silicon layer and an ohmic contact layer, and each second stacked structure at least includes said first conducting layer;  
a photo-imagable layer between said plurality of first stacked structures and said plurality of said second stacked structures so as to be contact with the first conducting layer, the insulation layer, the amorphous silicon layer and the ohmic contact layer;  
a source electrode and a drain electrode on said photo-imagable layer and said plurality of first stacked structures;  
a passivation layer on said amorphous silicon layer, said photo-imagable layer and said source electrode and said drain electrode; and  
a transparent electrode on said passivation layer wherein a first portion of said transparent electrode electrically connects to one of said source electrode and drain electrode, and a second portion of said transparent electrode electrically connects to said second conducting layer of said plurality of first stacked structures and said first conducting layer of said plurality of second stacked structure.

14-15. (Cancelled)

16. (New) The TFT structure according to claim 9, wherein the first conducting layer is disposed on the substrate, and the insulation layer, the amorphous silicon layer and the ohmic contact layer are successively stacked up on top of each other to be different in height.
17. (New) The TFT structure according to claim 13, wherein the first conducting layer is disposed on the substrate, and the insulation layer, the amorphous silicon layer and the ohmic contact layer are successively stacked up on top of each other to be different in height.
18. (New) The TFT structure according to claim 13, wherein the second stacked structures further include the insulation layer.
19. (New) The TFT structure according to claim 18, wherein the first conducting layer is disposed on the substrate, and the insulation layer is stacked up on top of the first conducting layer to be different in height.